

NTA7002N, NVTA7002N

MOSFET – Single, N-Channel, Small Signal, Gate ESD Protection, SC-75

30 V, 154 mA

Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players, Digital Cameras, PDA's, Video Games, Hand-Held Computers, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	30	V
Gate-to-Source Voltage	V _{GS}	±10	V
Continuous Drain Current (Note 1)	I _D	154	mA
Power Dissipation (Note 1)	P _D	300	mW
Pulsed Drain Current	I _{DM}	618	mA
Operating Junction and Storage Temperature	T _J , T _{STG}	-55 to 150	°C
Continuous Source Current (Body Diode)	I _{SD}	154	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	R _{θJA}	416	°C/W

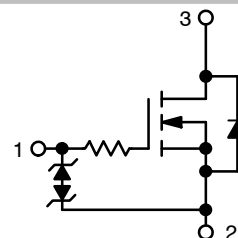
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



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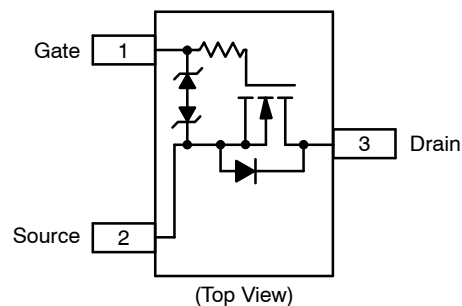
V _{(BR)DSS}	R _{DS(on)} Typ @ V _{GS}	I _D MAX (Note 1)
30 V	1.4 Ω @ 4.5 V	154 mA
	2.3 Ω @ 2.5 V	



N-Channel

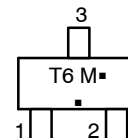
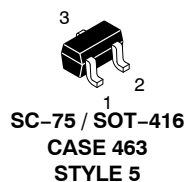
PIN CONNECTIONS

SC-75 (3-Leads)



(Top View)

MARKING DIAGRAM



T6 = Specific Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 100 μA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 30 V			1.0	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V, T = 85 °C			1.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±10 V			±25	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±5 V			±1.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±5 V T = 85 °C			±1.0	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 100 μA	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 154 mA		1.4	7.0	Ω
		V _{GS} = 2.5 V, I _D = 154 mA		2.3	7.5	
Forward Transconductance	g _{FS}	V _{DS} = 3 V, I _D = 154 mA		80		mS

CAPACITANCES

Input Capacitance	C _{ISS}	V _{DS} = 5.0 V, f = 1 MHz, V _{GS} = 0 V		11.5	20	pF
Output Capacitance	C _{OSS}			10	15	
Reverse Transfer Capacitance	C _{RSS}			3.5	6.0	

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 5.0 V, I _D = 75 mA, R _G = 10 Ω		13		ns
Rise Time	t _r			15		ns
Turn-Off Delay Time	t _{d(OFF)}			98		
Fall Time	t _f			60		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 154 mA		0.77	0.9	V
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2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

NTA7002N, NVTA7002N

TYPICAL PERFORMANCE CURVES

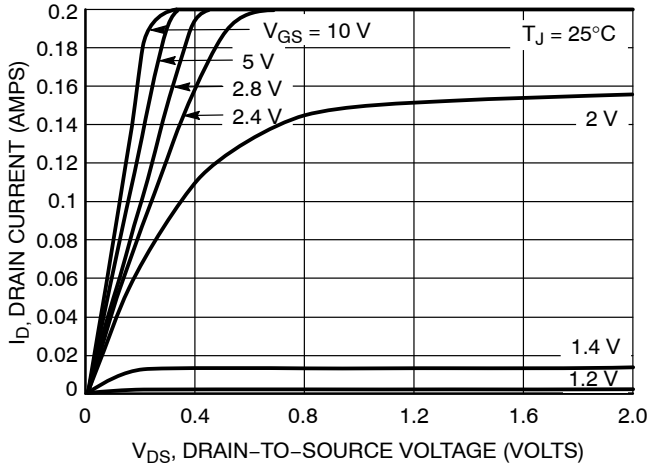


Figure 1. On-Region Characteristics

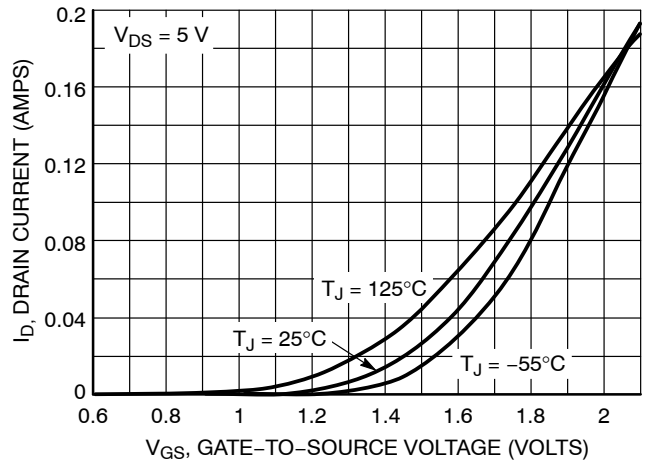


Figure 2. Transfer Characteristics

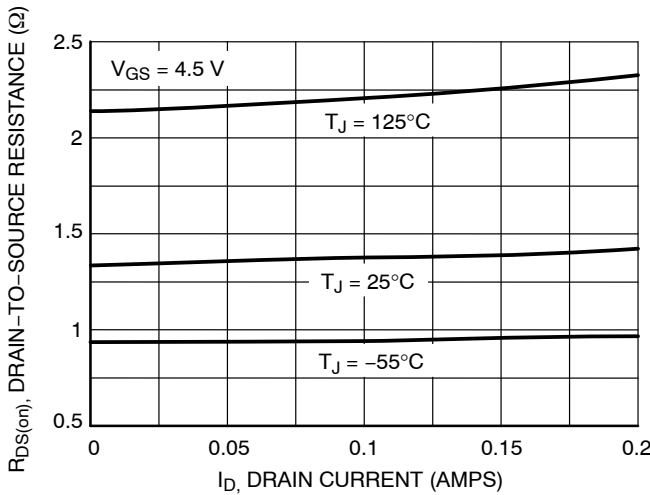


Figure 3. On-Resistance vs. Drain Current and Temperature

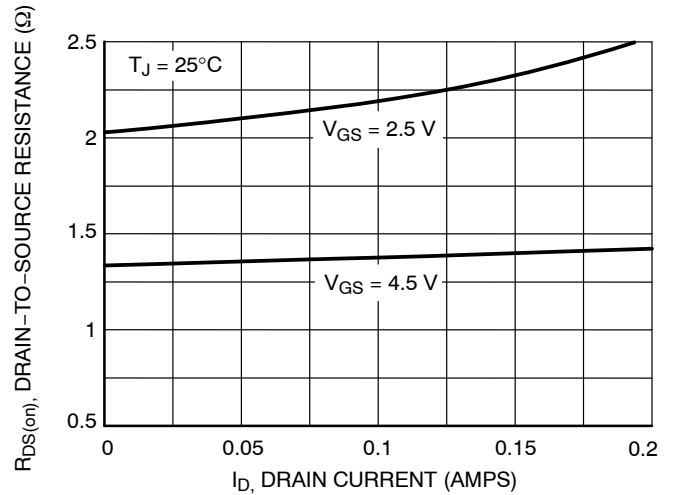


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

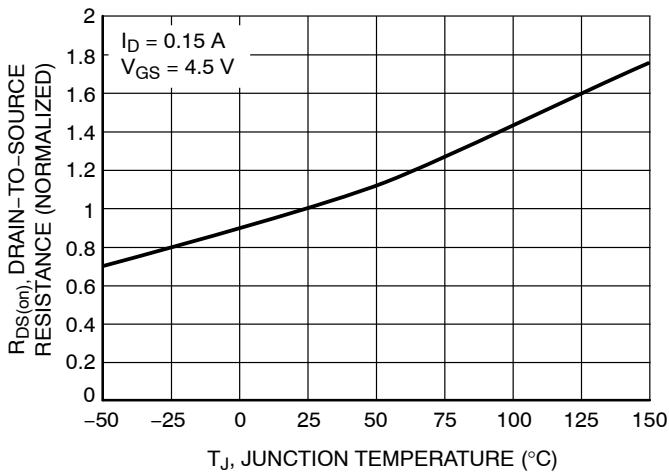


Figure 5. On-Resistance Variation with Temperature

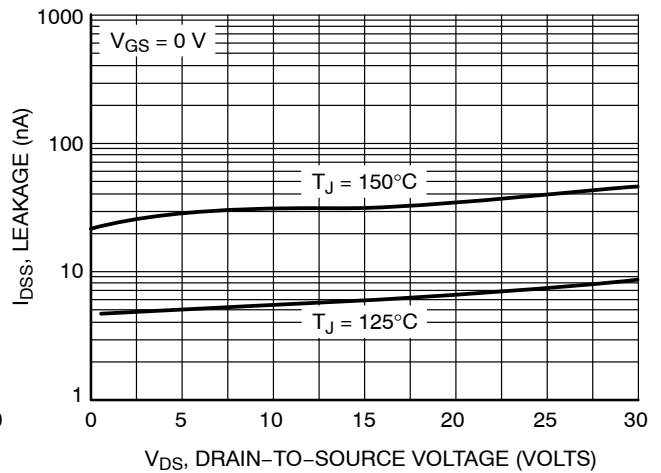
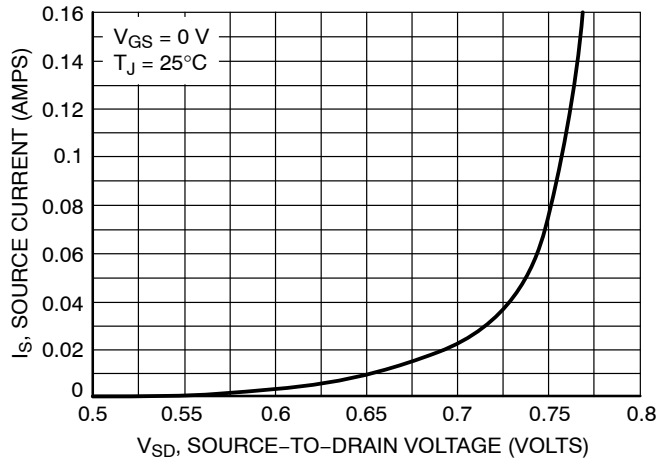
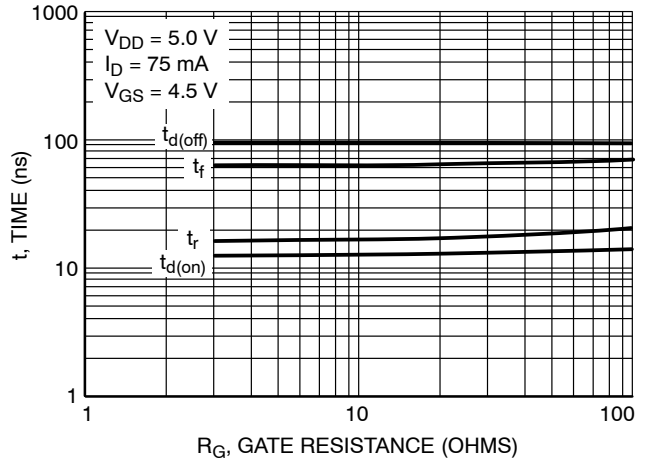
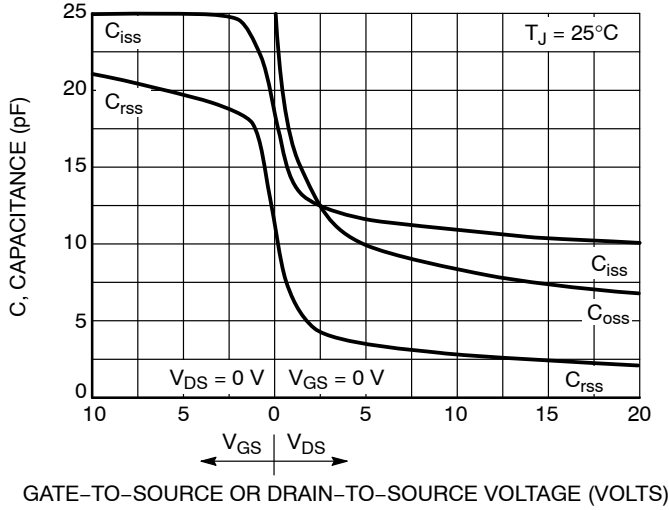


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTA7002N, NVTA7002N

TYPICAL PERFORMANCE CURVES



ORDERING INFORMATION

Device	Package	Shipping [†]
NTA7002NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel
NVTA7002NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

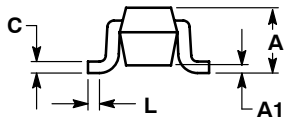
ON Semiconductor®



SC-75/SOT-416
CASE 463-01
ISSUE G

DATE 07 AUG 2015

SCALE 4:1



STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

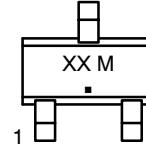
STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

GENERIC MARKING DIAGRAM*



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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